

Takashi Hanada

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

148
papers

2,604
citations

28
h-index

45
g-index

156
ext. papers

2,747
ext. citations

2.7
avg, IF

4.17
L-index

#	Paper	IF	Citations
148	Growth and scintillation properties of Ce doped 6LiBr/LaBr ₃ eutectic scintillator for neutron detection. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2022 , 166384	1.2	1
147	Crystal growth of La ₂ Hf ₂ O ₇ by micro-pulling-down method using W crucible. <i>Journal of Crystal Growth</i> , 2022 , 583, 126547	1.6	
146	Growth and scintillation properties of directionally solidified Ce:LaCl ₃ /AeCl ₂ (Ae = Mg, Ca, Sr) eutectic Scintillators. <i>Journal of Crystal Growth</i> , 2022 , 584, 126549	1.6	0
145	Growth of Tb-doped BaCl ₂ /NaCl/KCl ternary eutectic and its luminescence properties. <i>Journal of Crystal Growth</i> , 2022 , 580, 126467	1.6	0
144	sim-trhepd-rheed IDopen-source simulator of total-reflection high-energy positron diffraction (TRHEPD) and reflection high-energy electron diffraction (RHEED). <i>Computer Physics Communications</i> , 2022 , 277, 108371	4.2	0
143	Growth and scintillation properties of Tl-doped CsI/CsCl/NaCl ternary eutectic scintillators. <i>Japanese Journal of Applied Physics</i> , 2021 , 60, SBBK01	1.4	4
142	Crystal Growth of La ₂ Zr ₂ O ₇ by micro-pulling-down method using Mo and W crucibles. <i>Journal of Crystal Growth</i> , 2021 , 126357	1.6	1
141	Growth and scintillation properties of Tl-doped CsI/KI/KCl ternary eutectics. <i>Journal of Crystal Growth</i> , 2021 , 573, 126287	1.6	1
140	Dependence of the V/III Ratio on Indium Incorporation in InGaN Films Grown by Metalorganic Vapour Phase Epitaxy. <i>Journal of Nanoscience and Nanotechnology</i> , 2020 , 20, 2979-2986	1.3	2
139	Development of Data-Analysis Software for Total-Reflection High-Energy Positron Diffraction (TRHEPD). <i>Acta Physica Polonica A</i> , 2020 , 137, 188-192	0.6	4
138	Crystal growth and scintillation properties of tube shape-controlled Ce-doped Y ₃ Al ₅ O ₁₂ single crystals grown by micro-pulling-down method. <i>Applied Physics Express</i> , 2020 , 13, 125503	2.4	2
137	Thermodynamic model for metalorganic vapor-phase epitaxy of N-polar group-III nitrides in step-flow growth mode: Hydrogen, competitive adsorption, and configuration entropy. <i>Physical Review Materials</i> , 2019 , 3,	3.2	2
136	Characterization of the ScAlMgO ₄ cleaving layer by X-ray crystal truncation rod scattering. <i>Journal of Applied Physics</i> , 2018 , 123, 205305	2.5	7
135	Ga-polar GaN film grown by MOVPE on cleaved ScAlMgO ₄ (0001) substrate with millimeter-scale wide terraces. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600754	1.6	10
134	Polarity control of GaN grown on pulsed-laser-deposited AlN/GaN template by metalorganic vapor phase epitaxy. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 05FA04	1.4	4
133	Homogeneity improvement of N-polar $\{000\bar{1}\}$ InGaN/GaN multiple quantum wells by using c-plane sapphire substrate with off-cut-angle towards sapphire plane. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 05FA09	1.4	9
132	Suppression of metastable-phase inclusion in N-polar (0001) InGaN/GaN multiple quantum wells grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2015 , 106, 222102	3.4	5

131	Red to blue wavelength emission of N-polar $\{0001\}$ InGaN light-emitting diodes grown by metalorganic vapor phase epitaxy. <i>Applied Physics Express</i> , 2015 , 8, 061005	2.4	40
130	Improvement of surface morphology of nitrogen-polar GaN by introducing indium surfactant during MOVPE growth. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 085501	1.4	16
129	Enhancement of surface migration by Mg doping in the metalorganic vapor phase epitaxy of N-polar $\{0001\}$ GaN/sapphire. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 05FL05	1.4	12
128	Effect of c-plane sapphire substrate miscut angle on indium content of MOVPE-grown N-polar InGaN. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 05FL07	1.4	6
127	Investigation of indium incorporation into InGaN by nitridation of sapphire substrate in MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 417-420		3
126	Phase diagram on phase purity of InN grown pressurized-reactor MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 654-657		10
125	Effect of Nitridation on Indium-Composition of InGaN Films. <i>Key Engineering Materials</i> , 2012 , 508, 193-198		4
124	Tilted Domain and Indium Content of InGaN Layer on m -Plane GaN Substrate Grown by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 04DH01	1.4	3
123	Tilted Domain and Indium Content of InGaN Layer on m -Plane GaN Substrate Grown by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 04DH01	1.4	3
122	Strain relaxation mechanism of InGaN thin film grown on m -GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 444-446		12
121	Electrochemical isothermal-capacitance-transient spectroscopy: a new depth profiling method of deep levels. <i>Review of Scientific Instruments</i> , 2011 , 82, 093905	1.7	
120	An empirical equation including the strain effect for optical transition energy of strained and fully relaxed GaN films. <i>Journal Physics D: Applied Physics</i> , 2010 , 43, 175101	3	4
119	Effect of anion-to-cation supplying ratio on the surface morphology of AlN films grown on ZnO substrates at low temperature. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2010 , 28, 61-64	2.9	
118	Lattice strain in bulk GaN epilayers grown on CrN/sapphire template. <i>Applied Physics Letters</i> , 2009 , 94, 082105	3.4	41
117	X-ray photoelectron spectroscopy study on the CrN surface grown on sapphire substrate to control the polarity of ZnO by plasma-assisted molecular beam epitaxy. <i>Applied Surface Science</i> , 2009 , 255, 8582-8586	6.7	6
116	Effects of interfacial layer structures on crystal structural properties of ZnO films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2008 , 26, 90-96	2.9	25
115	Comparative study of photoluminescences for Zn-polar and O-polar faces of single-crystalline ZnO bulks. <i>Applied Physics Letters</i> , 2008 , 93, 241907	3.4	29
114	Optical properties and electrical properties of heavily Al-doped ZnSe layers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2008 , 26, 259-264	2.9	1

113	The effect of hydrogen irradiation and annealing on the low-temperature growth of homoepitaxial ZnO layers grown on (0 0 0 1) ZnO substrates by plasma-assisted molecular beam epitaxy. <i>Applied Surface Science</i> , 2008 , 254, 3120-3124	6.7	3
112	Growth of Polarity-Controlled ZnO Films on (0001) Al ₂ O ₃ . <i>Journal of Electronic Materials</i> , 2008 , 37, 736-743	14.2	13
111	Study of local segregation in GaInNAs using EXAFS measurements. <i>Journal of Physics and Chemistry of Solids</i> , 2008 , 69, 298-301	3.9	1
110	The high quality ZnO growth on c-Al ₂ O ₃ substrate with Cr ₂ O ₃ buffer layer using plasma-assisted molecular beam epitaxy. <i>Applied Surface Science</i> , 2008 , 254, 7786-7789	6.7	7
109	Structural investigation of nitrated c-sapphire substrate by grazing incidence x-ray diffraction and transmission electron microscopy. <i>Applied Physics Letters</i> , 2007 , 91, 202116	3.4	7
108	Molecular beam epitaxy and magnetic properties of GaMnNAs. <i>Journal of Crystal Growth</i> , 2007 , 301-302, 642-646	1.6	4
107	Analysis of the relation between leakage current and dislocations in GaN-based light-emitting devices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 37-40		5
106	Structural characterization of MgO/c-Al ₂ O ₃ interfaces. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 1715-1718		1
105	Characterization of free-standing GaN substrates prepared by self lift-off. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 2617-2620		1
104	Metal catalyst enhanced growth of high quality and density GaN dots on Si(111) by implant source growth. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 2314-2317		1
103	Lattice relaxation mechanism of ZnO thin films grown on c-Al ₂ O ₃ substrates by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2007 , 91, 231904	3.4	43
102	Strain-free GaN thick films grown on single crystalline ZnO buffer layer with in situ lift-off technique. <i>Applied Physics Letters</i> , 2007 , 90, 061907	3.4	22
101	Impact of V/III ratio on electrical properties of GaN thick films grown by hydride vapor-phase epitaxy. <i>Applied Physics Letters</i> , 2007 , 91, 132112	3.4	23
100	Crystal Growth 2007 , 329-445		0
99	Polarity control of ZnO films on (0001) Al ₂ O ₃ by Cr-compound intermediate layers. <i>Applied Physics Letters</i> , 2007 , 90, 201907	3.4	44
98	Photoresponsivity of ZnO Schottky barrier diodes. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 1595		13
97	Origin of forward leakage current in GaN-based light-emitting devices. <i>Applied Physics Letters</i> , 2006 , 89, 132117	3.4	128
96	Slowdown in development of self-assembled InAs/GaAs(001) dots near the critical thickness. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 1886		3

95	Correlation between ZnO Nanowire Growth and the Surface of AlN Substrate. <i>Crystal Growth and Design</i> , 2006 , 6, 2640-2642	3.5	4
94	Ordering of In and Ga in Epitaxially Grown In _{0.53} Ga _{0.47} As Films on (001) InP Substrates. <i>Materials Transactions</i> , 2006 , 47, 1115-1120	1.3	2
93	Electrical properties of ZnO/GaN heterostructures and photoresponsivity of ZnO layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 946-951		13
92	Observation of a filled electronic state in the conduction band of InN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 1846-1849		6
91	Novel method for site-controlled surface nanodot fabrication by ion beam synthesis. <i>Nano Letters</i> , 2005 , 5, 771-6	11.5	23
90	Structural variation of cubic and hexagonal Mg _x Zn _{1-x} O layers grown on MgO(111)-sapphire. <i>Journal of Applied Physics</i> , 2005 , 98, 054911	2.5	98
89	Capacitance-voltage characteristics of ZnO/GaN heterostructures. <i>Applied Physics Letters</i> , 2005 , 87, 1621-1624	1.4	21
88	Formation and evolution of strain-induced self-assembled dot. <i>Microelectronics Journal</i> , 2005 , 36, 216-218	1.8	4
87	GaN nanodot fabrication by implant source growth. <i>Microelectronics Journal</i> , 2005 , 36, 456-459	1.8	3
86	Soft X-ray spectroscopy of diluted magnetic semiconductor Ga _{1-x} M _x N (M = Cr, Mn). <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2005 , 144-147, 707-710	1.7	2
85	Electronic structure of the Ga _{1-x} Cr _x N studied by high-energy photoemission spectroscopy. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2005 , 144-147, 561-564	1.7	2
84	GaNAs(001) surface phases under growing condition. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005 , 23, 1341		
83	Electron-trap centers in ZnO layers grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2005 , 86, 032909	3.4	42
82	Characteristics of Schottky contacts to ZnO:N layers grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2005 , 86, 042110	3.4	39
81	Electrical characterization for ZnO layers grown on GaN templates by molecular-beam epitaxy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005 , 23, 1281		4
80	Experimental demonstration of Fano-type resonance in photoluminescence of ZnS:MnBiO ₂ one-dimensional photonic crystals. <i>Applied Physics Letters</i> , 2005 , 87, 171106	3.4	6
79	Structure and magnetic properties of Cr-doped GaN. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005 , 23, 1308		23
78	Hybridization of Cr 3d and Ga 4s in the wide band-gap diluted magnetic semiconductor Ga _{1-x} Cr _x N. <i>Physical Review B</i> , 2004 , 70,	3.3	17

77	Deep-level-transient spectroscopy of heavily Al-doped ZnSe layers grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2004 , 96, 7332-7337	2.5	7
76	Optical anisotropy of GaNAs grown on GaAs(001) substrate. <i>Current Applied Physics</i> , 2004 , 4, 640-642	2.6	1
75	Optical anisotropy and surface morphology of InGaAs lattice-mismatched with GaAs(001). <i>Current Applied Physics</i> , 2004 , 4, 621-624	2.6	
74	Characterization of N-doped ZnO layers grown on (0001) GaN/Al ₂ O ₃ substrates by molecular beam epitaxy. <i>Current Applied Physics</i> , 2004 , 4, 625-629	2.6	10
73	Surface structure of InGaAs/InP(0 0 1) ordered alloy during and after growth. <i>Applied Surface Science</i> , 2004 , 237, 230-234	6.7	7
72	Optimization of ZnSe growth on miscut GaAs substrates by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2003 , 249, 128-143	1.6	21
71	MBE growth and characterization of A-site deficient, low-field magnetoresistance (Pr _{1-x} Sr _x) _y MnO ₃ oriented thin films. <i>Journal of Crystal Growth</i> , 2003 , 251, 619-622	1.6	1
70	Characteristics of deep levels in Al-doped ZnSe grown by molecular beam epitaxy. <i>Materials Science in Semiconductor Processing</i> , 2003 , 6, 567-571	4.3	6
69	High-energy photoemission spectroscopy of ferromagnetic Ga _{1-x} Mn _x N. <i>Materials Science in Semiconductor Processing</i> , 2003 , 6, 503-506	4.3	5
68	Growth and characterization of Ga _{1-x} Cr _x N with high Cr content grown on ZnO templates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2869-2873		14
67	Measurements of a component of the piezo-optic tensor of Si by reflectance difference spectroscopy. <i>Journal of Applied Physics</i> , 2003 , 94, 1458-1460	2.5	2
66	Realization of one-chip-multiple-wavelength laser diodes with II _{VI} /III _{IV} compound semiconductors. <i>Applied Physics Letters</i> , 2003 , 82, 4095-4097	3.4	3
65	Molecular Beam Epitaxy of Al Doped n-ZnSe. <i>Physica Status Solidi (B): Basic Research</i> , 2002 , 229, 381-384	1.3	14
64	Measurements of the Linear Electro-Optic Coefficients of ZnTe by RDS. <i>Physica Status Solidi (B): Basic Research</i> , 2002 , 229, 605-609	1.3	1
63	ZnTe-Based Light-Emitting-Diodes Grown on ZnTe Substrates by Molecular Beam Epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2002 , 229, 995-999	1.3	36
62	X-ray diffraction characterization of MBE grown Pr _{1-x} Sr _x MnO ₃ thin films on NGO(1 1 0). <i>Applied Surface Science</i> , 2002 , 190, 408-415	6.7	5
61	Control of polarity of heteroepitaxial ZnO films by interface engineering. <i>Applied Surface Science</i> , 2002 , 190, 491-497	6.7	20
60	Improvement in crystallinity of ZnSe by inserting a low-temperature buffer layer between the ZnSe epilayer and the GaAs substrate. <i>Journal of Crystal Growth</i> , 2002 , 242, 95-103	1.6	20

59	Determination of carrier concentration in n-ZnSe by reflectance difference spectroscopy: Experimental results and model calculation. <i>Journal of Applied Physics</i> , 2002 , 92, 139-143	2.5	6
58	Formation processes of CdTe quantum dots on ZnTe substrates studied by reflection high-energy electron diffraction and photoluminescence. <i>Journal of Applied Physics</i> , 2002 , 92, 5490-5493	2.5	7
57	Atomic structure of the GaAs(001)($\sqrt{3}\times\sqrt{3}$) surface under As flux. <i>Physical Review B</i> , 2002 , 65,	3.3	53
56	Correlation of surface chemistry of GaAs substrates with growth mode and stacking fault density in ZnSe epilayers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2002 , 20, 1948	2.9	2
55	Control of crystal polarity in a wurtzite crystal: ZnO films grown by plasma-assisted molecular-beam epitaxy on GaN. <i>Physical Review B</i> , 2002 , 65,	3.3	94
54	Structural characteristic and magnetic properties of Mn oxide films grown by plasma-assisted MBE. <i>Journal of Crystal Growth</i> , 2001 , 227-228, 955-959	1.6	17
53	Growth of PrSrMnO ₃ -like thin films on NGO (110) substrates by plasma assisted MBE. <i>Journal of Crystal Growth</i> , 2001 , 227-228, 960-965	1.6	1
52	ZnO epilayers on GaN templates: Polarity control and valence-band offset. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001 , 19, 1429		28
51	Structural characteristics and magnetic properties of ϵ -MnO ₂ films grown by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2001 , 90, 351-354	2.5	18
50	Surface structures of GaAs{111}A,B($\sqrt{3}\times\sqrt{3}$). <i>Physical Review B</i> , 2001 , 64,	3.3	69
49	Effect of lattice mismatch on surface morphology of InAs quantum dots on (100) In _{1-x} Al _x As/InP. <i>Applied Physics Letters</i> , 2001 , 79, 4331-4333	3.4	13
48	Band alignment at a ZnO/GaN (0001) heterointerface. <i>Applied Physics Letters</i> , 2001 , 78, 3349-3351	3.4	114
47	Low stacking-fault density in ZnSe epilayers directly grown on epi-ready GaAs substrates without GaAs buffer layers. <i>Applied Physics Letters</i> , 2001 , 78, 165-167	3.4	46
46	Strain Relaxation of Self-Assembled InAs/GaAs(001) Quantum Dots Observed by Reflection High-Energy Electron Diffraction. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, 1878-1881	1.4	15
45	Anisotropic shape of self-assembled InAs quantum dots: Refraction effect on spot shape of reflection high-energy electron diffraction. <i>Physical Review B</i> , 2001 , 64,	3.3	45
44	Evolution of initial layers of plasma-assisted MBE grown ZnO on (0001)GaN/sapphire. <i>Journal of Crystal Growth</i> , 2000 , 214-215, 81-86	1.6	27
43	In situ measurement of carrier concentration in n-ZnSe by reflectance difference spectroscopy (RDS). <i>Journal of Crystal Growth</i> , 2000 , 214-215, 547-551	1.6	6
42	Self-organized formation processes of CdSe quantum dots studied by reflection high-energy electron diffraction. <i>Journal of Crystal Growth</i> , 2000 , 214-215, 703-706	1.6	7

41	Growth of GaN single crystals from a NaGa melt at 750°C and 5MPa of N ₂ . <i>Journal of Crystal Growth</i> , 2000 , 218, 7-12	1.6	60
40	Surface reconstruction and crystal structure of MgSe films grown on ZnTe substrates by MBE. <i>Journal of Crystal Growth</i> , 2000 , 208, 253-258	1.6	13
39	Effects of a low-temperature buffer layer on structural properties of ZnO epilayers grown on (111)CaF ₂ by two-step MBE. <i>Journal of Crystal Growth</i> , 2000 , 208, 389-394	1.6	19
38	Control and characterization of ZnO/GaN heterointerfaces in plasma-assisted MBE-grown ZnO films on GaN/Al ₂ O ₃ . <i>Applied Surface Science</i> , 2000 , 159-160, 441-448	6.7	28
37	Adsorption processes of Se on the GaAs(111)A(√2×√2) surface. <i>Applied Surface Science</i> , 2000 , 162-163, 419-424	6.7	2
36	Control of polarity of ZnO films grown by plasma-assisted molecular-beam epitaxy: Zn- and O-polar ZnO films on Ga-polar GaN templates. <i>Applied Physics Letters</i> , 2000 , 77, 3571-3573	3.4	60
35	Observation of bulk Bragg-reflection using reflection high-energy electron diffraction on Mn ₃ O ₄ -like films grown on MgO (001) by molecular beam epitaxy. <i>Surface Science</i> , 2000 , 445, 151-158	1.8	7
34	Structure and composition of the ZnSe(001) surface during atomic-layer epitaxy. <i>Physical Review B</i> , 1999 , 60, 8326-8332	3.3	34
33	In situ observation of strain-induced optical anisotropy of Zn _{Sx} Se _{1-x} /GaAs(110) during molecular-beam epitaxy. <i>Physical Review B</i> , 1999 , 60, 8909-8914	3.3	8
32	Real-time analysis of adsorption processes of Zn on the GaAs(001)(√3×√3) surface. <i>Physical Review B</i> , 1999 , 60, 8713-8718	3.3	17
31	Adsorption of Zn on the GaAs(001)-(√3×√3) surface. <i>Applied Physics Letters</i> , 1999 , 74, 2975-2977	3.4	9
30	Self-assembled formation of ZnCdSe quantum dots on atomically smooth ZnSe surfaces on GaAs(001) by molecular beam epitaxy. <i>Thin Solid Films</i> , 1999 , 357, 1-7	2.2	10
29	Atomic layer epitaxy processes of ZnSe on GaAs(0 0 1) as observed by beam-rocking reflection high-energy electron diffraction (RHEED) and total-reflection-angle X-ray spectroscopy (TRAXS). <i>Journal of Crystal Growth</i> , 1999 , 201-202, 490-493	1.6	6
28	Two-step MBE growth of ZnO layers on electron beam exposed (111)CaF ₂ . <i>Journal of Crystal Growth</i> , 1999 , 207, 87-94	1.6	35
27	Structure of Se-adsorbed GaAs(111)A-(√3×√3)-R30° surface. <i>Physical Review B</i> , 1999 , 59, 8032-8036	3.3	16
26	Scanning tunneling microscopy study of the initial reaction of SiH ₂ Cl ₂ molecules with the Si(111)-7×7 surface. <i>Applied Surface Science</i> , 1998 , 130-132, 23-28	6.7	4
25	Properties of self-organized CdSe quantum dots on an atomically flat (111)A ZnSe surface. <i>Applied Surface Science</i> , 1998 , 130-132, 755-759	6.7	2
24	Electron Standing Wave at a Surface during Reflection High Energy Electron Diffraction and Adatom Height Determination. <i>Physical Review Letters</i> , 1995 , 75, 669-672	7.4	12

23	Rocking-curve analysis of reflection high-energy electron diffraction from the Si(111)-(sqrt 3 x sqrt 3)R30 degrees-Al, -Ga, and -In surfaces. <i>Physical Review B</i> , 1995 , 51, 13320-13325	3.3	68
22	Atomic layer control in Sr-Cu-O artificial lattice growth. <i>Applied Physics Letters</i> , 1994 , 65, 1717-1719	3.4	20
21	Surface reactions at the controlled structure of SrTiO3(001). <i>Surface and Interface Analysis</i> , 1994 , 22, 412-416	1.5	29
20	Layer controlled growth of oxide superconductors. <i>Applied Surface Science</i> , 1994 , 82-83, 487-493	6.7	17
19	Study of the Si(111)7x7 surface by RHEED rocking curve analysis. <i>Surface Science</i> , 1994 , 313, 143-154	1.8	48
18	Structure and electronic state of the TiO2 and SrO terminated SrTiO3(100) surfaces. <i>Surface Science</i> , 1993 , 287-288, 377-381	1.8	129
17	Surface structure of SrTiO3(001) with various surface treatments. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1993 , 11, 2649-2654	2.9	46
16	Atomic Layer Growth of SrCuO2 Thin Film by Molecular Beam Epitaxy.. <i>Hyomen Kagaku</i> , 1993 , 14, 283-287		1
15	Glancing Angle Dependence of the X-Ray Emission Measured under Total Reflection Angle X-Ray Spectroscopy (TRAXS) Condition during Reflection High Energy Electron Diffraction Observation. <i>Japanese Journal of Applied Physics</i> , 1992 , 31, L1503-L1505	1.4	11
14	Molecular beam epitaxial growth of superconducting Ba2DyCu3O6.5 thin films at 420 °C using NO2 as an oxidant. <i>Applied Physics Letters</i> , 1992 , 61, 1971-1973	3.4	14
13	Reaction between copper dipivaloylmethanate Cu(DPM)2 and H2O adsorbed on SrTiO3(100). <i>Surface Science</i> , 1992 , 262, L139-L143	1.8	8
12	Ultra thin film of Bi cuprate grown by a low temperature molecular beam epitaxy. <i>Physica C: Superconductivity and Its Applications</i> , 1991 , 185-189, 2057-2058	1.3	
11	Molecular beam epitaxy of Bi2Sr2CuOx and Bi2Sr2Ca0.85Sr0.15Cu2Ox ultra thin films at 300°C. <i>Journal of Crystal Growth</i> , 1991 , 112, 745-752	1.6	57
10	Structure and growth mechanism of ultrathin films of Bi cuprates grown by low-temperature MBE. <i>Physica C: Superconductivity and Its Applications</i> , 1991 , 190, 27-30	1.3	5
9	Selective surface reaction between metal compounds and surface functional groups. <i>Physica C: Superconductivity and Its Applications</i> , 1991 , 190, 148-150	1.3	1
8	Study of successive phase transitions of the Si(001)-Bi surface by RHEED. <i>Surface Science</i> , 1991 , 242, 137-142	1.8	42
7	The reaction of copper and calcium dipivaloylmethanates (Cu(DPM)2 and Ca(DPM)2) with hydroxyls on oxide surface. <i>Surface Science</i> , 1991 , 242, 508-512	1.8	22
6	Surface structure and oxidation of Si(001)Bi. <i>Vacuum</i> , 1990 , 41, 650-651	3.7	15

5	Molecular Beam Epitaxy Study of Bi ₂ Sr ₂ CuO _x Using NO ₂ as an Oxidizing Agent. <i>Japanese Journal of Applied Physics</i> , 1990 , 29, L1111-L1113	1.4	48
4	Ultrathin film of Bi ₂ Sr ₂ CuO _x formed by molecular beam epitaxy using NO ₂ . <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1990 , 8, 4104-4105	2.9	12
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